

NB : (1) **Q.1** is **Compulsory**.

(2) Attempt **any three** questions out of remaining **five**.

(3) Draw neat labelled diagram wherever necessary.

(4) For layouts use graph paper.

(5) Assumptions should be clearly mentioned.

1.

- (a) Differentiate between behaviour, data flow and structural style of architecture in VHDL. **5**
- (b) Write VHDL code for 2:4 decoder using process statement in behavioral style modelling. **5**
- (c) What is meant by latch up in CMOS. **5**
- (d) Explain various MOS capacitance. **5**

2.

- (a) Explain the architecture of FPGA. Explain the configurable logic block and input output block (IOB) of XC 4000 FPGA **10**
- (b) What are the various types of operators used in VHDL. **5**
- (c) Explain briefly various data types used in VHDL. **5**

3.

- (a) Write VHDL code for 4 bit full adder. **10**
- (b) PMOS transistor was fabricated on n-type substrate with bulk doping density of $N_D=10^{16}/\text{cm}^3$, gate doping density (n-type poly) of $N_D = 10^{20}/\text{cm}^3$, $N_{ox} = 4 \times 10^{10}/\text{cm}^2$ and oxide thickness of $t_{ox} = 0.1\mu\text{m}$. Calculate the threshold voltage at room temperature. $\epsilon_{si} = 11.7 \times \epsilon_0$, $\epsilon_{ox} = 3.97 \times \epsilon_0$, $\epsilon_0 = 8.854 \times 10^{-14} \text{ F/cm}$. **10**

4.

- (a) Design the circuit described by the function $y = \overline{(D + E + A)(B + C)}$ using CMOS and NMOS logic also draw stick diagram. **10**
- (b) Compare the constant voltage and constant field scaling. Show analytically how drain current, power dissipation and power density affected by the scaling. **10**

5. Explain briefly the following semi conductor manufacturing process. **20**
- (a) Oxidation
 - (b) Diffusion
 - (c) ion implantation
 - (d) metalisation
 - (e) etching
6. (a) Draw the circuit diagram, stick diagram and λ - based layout for 2 input NOR gate **10**
with depletion MOSFET as load, with aspect ratio of driver is 1:2 and load is 2:1.
- (b) Draw the transfer characteristic of CMOS inverter and explain the operating **5**
regions of NMOS and PMOS transistor at various point in transfer characteristics.
- (c) What is meant by noise margin in inverter. **5**
